



# BUK7K25-40E

Dual N-channel TrenchMOS standard level FET

23 April 2013

Product data sheet

## 1. General description

Dual standard level N-channel MOSFET in a LPAK56D package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

## 2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with  $V_{GS(th)} > 1 \text{ V @ } 175 \text{ °C}$

## 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

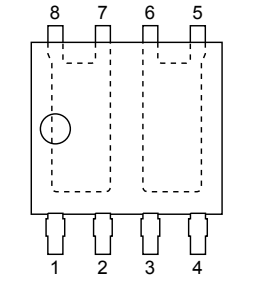
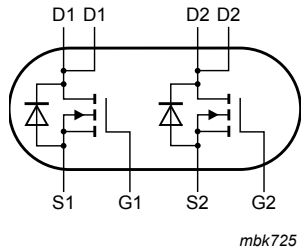
## 4. Quick reference data

Table 1. Quick reference data

| Symbol                                       | Parameter                        | Conditions                                                                                                             | Min | Typ   | Max | Unit |
|----------------------------------------------|----------------------------------|------------------------------------------------------------------------------------------------------------------------|-----|-------|-----|------|
| $V_{DS}$                                     | drain-source voltage             | $T_j \geq 25 \text{ °C}; T_j \leq 175 \text{ °C}$                                                                      | -   | -     | 40  | V    |
| $I_D$                                        | drain current                    | $V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{Fig. 1}$                                                         | -   | -     | 27  | A    |
| $P_{tot}$                                    | total power dissipation          | $T_{mb} = 25 \text{ °C}; \text{Fig. 2}$                                                                                | -   | -     | 32  | W    |
| <b>Static characteristics FET1 and FET2</b>  |                                  |                                                                                                                        |     |       |     |      |
| $R_{DS(on)}$                                 | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; \text{Fig. 12}$                                        | -   | 21.25 | 25  | mΩ   |
| <b>Dynamic characteristics FET1 and FET2</b> |                                  |                                                                                                                        |     |       |     |      |
| $Q_{GD}$                                     | gate-drain charge                | $I_D = 5 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}; \text{Fig. 14}; \text{Fig. 15}$ | -   | 2.6   | -   | nC   |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline                                                                                      | Graphic symbol                                                                                |
|-----|--------|-------------|---------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------|
| 1   | S1     | source1     | <br>LFPAK56D (SOT1205) | <br>mbk725 |
| 2   | G1     | gate1       |                                                                                                         |                                                                                               |
| 3   | S2     | source2     |                                                                                                         |                                                                                               |
| 4   | G2     | gate2       |                                                                                                         |                                                                                               |
| 5   | D2     | drain2      |                                                                                                         |                                                                                               |
| 6   | D2     | drain2      |                                                                                                         |                                                                                               |
| 7   | D1     | drain1      |                                                                                                         |                                                                                               |
| 8   | D1     | drain1      |                                                                                                         |                                                                                               |

6. Ordering information

Table 3. Ordering information

| Type number | Package  |                                                                  |         |
|-------------|----------|------------------------------------------------------------------|---------|
|             | Name     | Description                                                      | Version |
| BUK7K25-40E | LFPAK56D | Plastic single ended surface mounted package (LFPAK56D); 8 leads | SOT1205 |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BUK7K25-40E | 72540E       |

8. Limiting values

Table 5. Limiting values

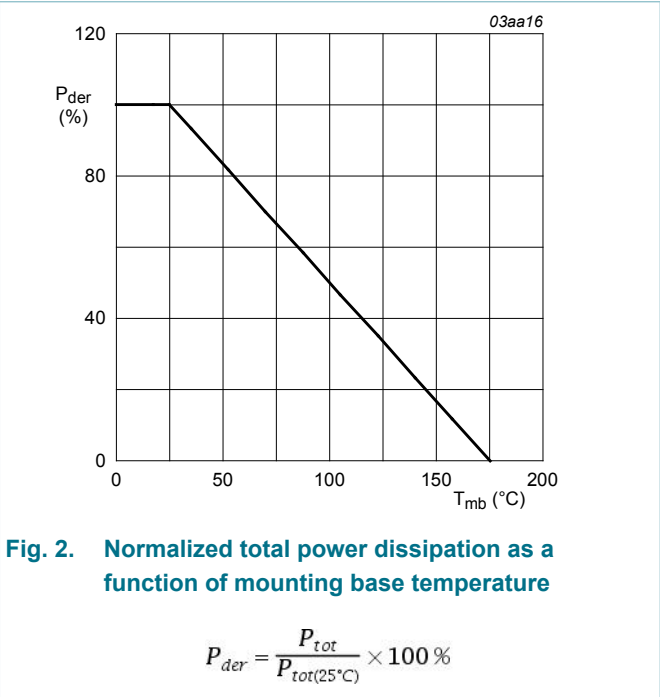
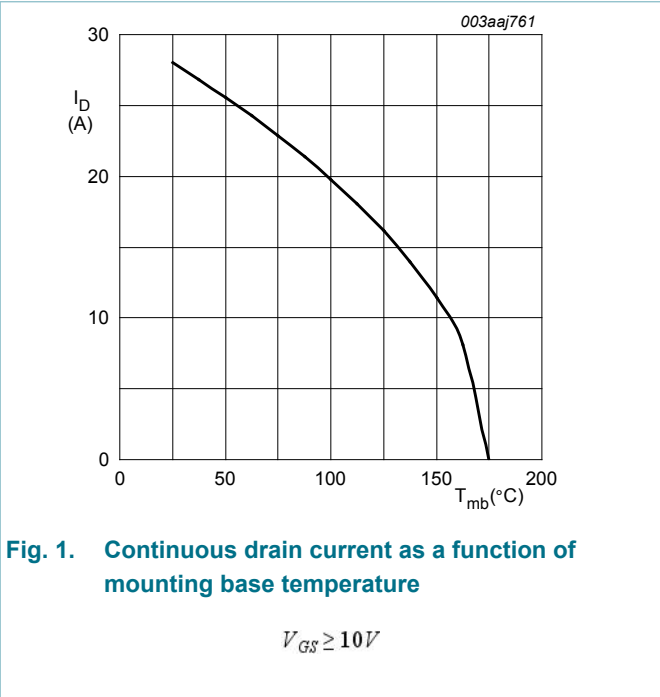
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter               | Conditions                                                                                                    |  | Min | Max | Unit |
|-----------|-------------------------|---------------------------------------------------------------------------------------------------------------|--|-----|-----|------|
| $V_{DS}$  | drain-source voltage    | $T_j \geq 25\text{ }^{\circ}\text{C}$ ; $T_j \leq 175\text{ }^{\circ}\text{C}$                                |  | -   | 40  | V    |
| $V_{DGR}$ | drain-gate voltage      | $R_{GS} = 20\text{ k}\Omega$ ; $T_j \geq 25\text{ }^{\circ}\text{C}$ ; $T_j \leq 175\text{ }^{\circ}\text{C}$ |  | -   | 40  | V    |
| $V_{GS}$  | gate-source voltage     | $T_j \leq 175\text{ }^{\circ}\text{C}$ ; DC                                                                   |  | -20 | 20  | V    |
| $I_D$     | drain current           | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; Fig. 1                                       |  | -   | 27  | A    |
|           |                         | $T_{mb} = 100\text{ }^{\circ}\text{C}$ ; $V_{GS} = 10\text{ V}$ ; Fig. 1                                      |  | -   | 19  | A    |
| $I_{DM}$  | peak drain current      | $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; Fig. 4                     |  | -   | 107 | A    |
| $P_{tot}$ | total power dissipation | $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; Fig. 2                                                                |  | -   | 32  | W    |

| Symbol                             | Parameter                                    | Conditions                                                                                                                      |                                         | Min | Max | Unit |
|------------------------------------|----------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------|-----|-----|------|
| T <sub>stg</sub>                   | storage temperature                          |                                                                                                                                 |                                         | -55 | 175 | °C   |
| T <sub>j</sub>                     | junction temperature                         |                                                                                                                                 |                                         | -55 | 175 | °C   |
| T <sub>slid(M)</sub>               | peak soldering temperature                   |                                                                                                                                 |                                         | -   | 260 | °C   |
| Source-drain diode FET1 and FET2   |                                              |                                                                                                                                 |                                         |     |     |      |
| I <sub>S</sub>                     | source current                               | T <sub>mb</sub> = 25 °C                                                                                                         |                                         | -   | 27  | A    |
| I <sub>SM</sub>                    | peak source current                          | pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C                                                                         |                                         | -   | 107 | A    |
| Avalanche Ruggedness FET1 and FET2 |                                              |                                                                                                                                 |                                         |     |     |      |
| E <sub>DS(AL)S</sub>               | non-repetitive drain-source avalanche energy | I <sub>D</sub> = 28 A; V <sub>sup</sub> ≤ 40 V; V <sub>GS</sub> = 10 V;<br>T <sub>j(init)</sub> = 25 °C; <a href="#">Fig. 3</a> | <a href="#">[1]</a> <a href="#">[2]</a> | -   | 10  | mJ   |

[1] Refer to application note AN10273 for further information

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



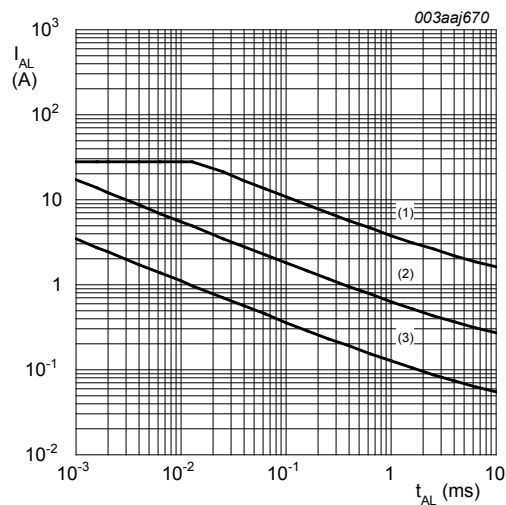


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

- (1) Single-pulse;  $T_j = 25\text{ }^{\circ}\text{C}$ .
- (2) Single-pulse;  $T_j = 150\text{ }^{\circ}\text{C}$ .
- (3) Repetitive.

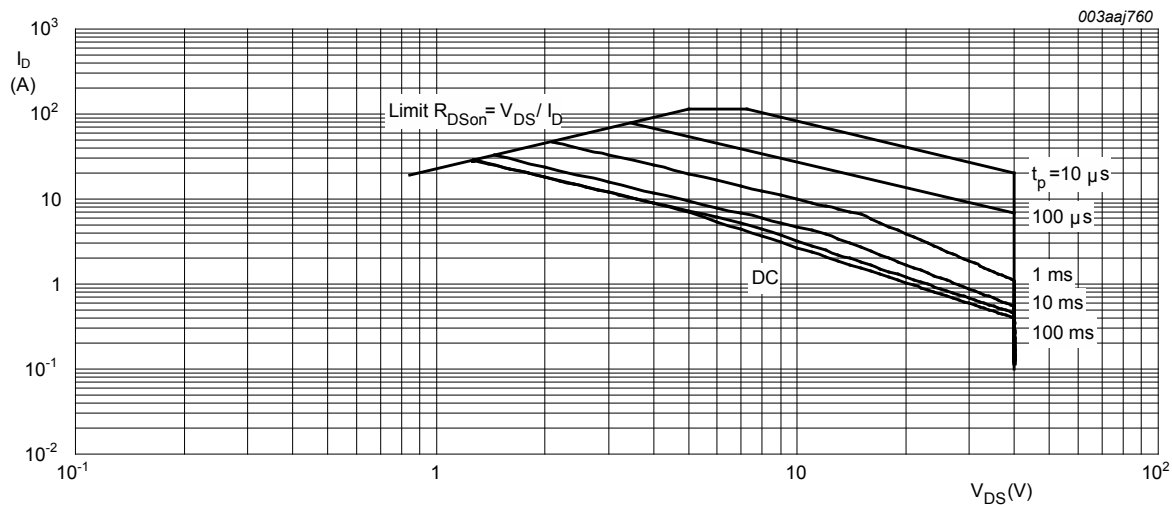


Fig. 4. Safe operating area; continuous and peak drain current as a function of drain-source voltage

$T_{mb} = 25\text{ }^{\circ}\text{C}$ ;  $I_{DM}$  is single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                         | Conditions | Min | Typ | Max  | Unit |
|----------------|---------------------------------------------------|------------|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5     | -   | -   | 4.68 | K/W  |

| Symbol        | Parameter                                   | Conditions                                            | Min | Typ | Max | Unit |
|---------------|---------------------------------------------|-------------------------------------------------------|-----|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | Minimum footprint; mounted on a printed circuit board | -   | 95  | -   | K/W  |

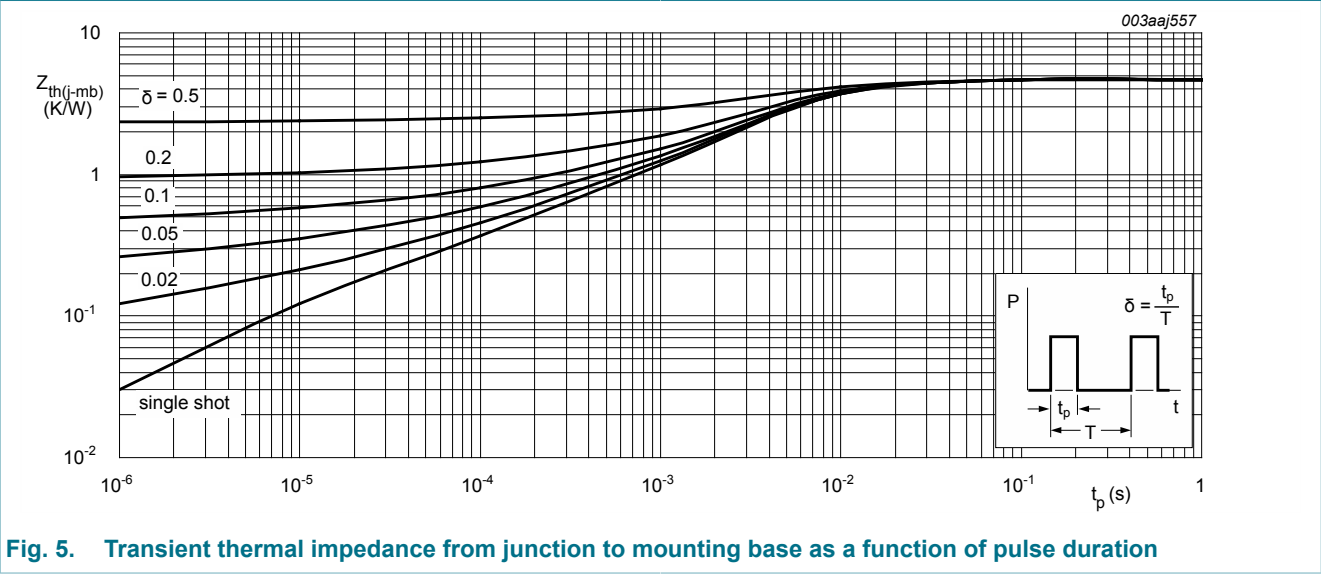


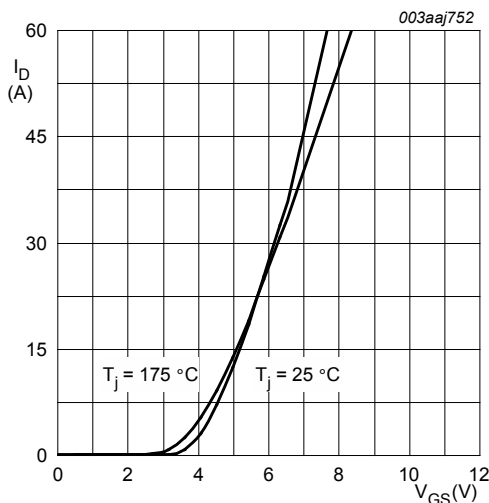
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

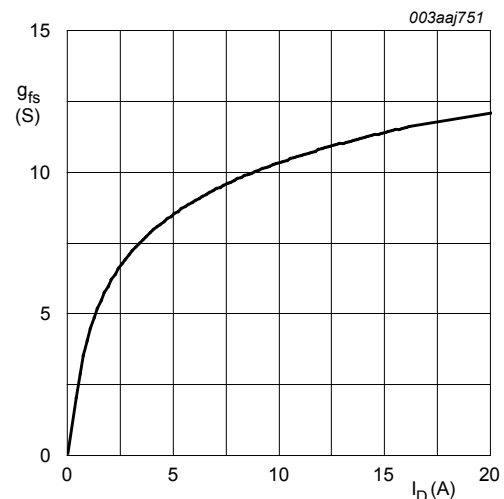
| Symbol                               | Parameter                        | Conditions                                                                                         | Min | Typ   | Max  | Unit          |
|--------------------------------------|----------------------------------|----------------------------------------------------------------------------------------------------|-----|-------|------|---------------|
| Static characteristics FET1 and FET2 |                                  |                                                                                                    |     |       |      |               |
| $V_{(BR)DSS}$                        | drain-source breakdown voltage   | $I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_J = -55\text{ }^\circ\text{C}$         | 36  | -     | -    | V             |
|                                      |                                  | $I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$          | 40  | -     | -    | V             |
| $V_{GS(th)}$                         | gate-source threshold voltage    | $I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; Fig. 10; Fig. 11      | 2.4 | 3     | 4    | V             |
|                                      |                                  | $I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_J = 175\text{ }^\circ\text{C}$ ; Fig. 10; Fig. 11     | 1   | -     | -    | V             |
|                                      |                                  | $I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_J = -55\text{ }^\circ\text{C}$ ; Fig. 10; Fig. 11     | -   | -     | 4.5  | V             |
| $I_{DSS}$                            | drain leakage current            | $V_{DS} = 40\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_J = 175\text{ }^\circ\text{C}$                 | -   | -     | 500  | $\mu\text{A}$ |
|                                      |                                  | $V_{DS} = 40\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$                  | -   | 0.02  | 1    | $\mu\text{A}$ |
| $I_{GSS}$                            | gate leakage current             | $V_{GS} = -20\text{ V}$ ; $V_{DS} = 0\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$                 | -   | 2     | 100  | nA            |
|                                      |                                  | $V_{GS} = 20\text{ V}$ ; $V_{DS} = 0\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$                  | -   | 2     | 100  | nA            |
| $R_{DSon}$                           | drain-source on-state resistance | $V_{GS} = 10\text{ V}$ ; $I_D = 5\text{ A}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; Fig. 12           | -   | 21.25 | 25   | m $\Omega$    |
|                                      |                                  | $V_{GS} = 10\text{ V}$ ; $I_D = 5\text{ A}$ ; $T_J = 175\text{ }^\circ\text{C}$ ; Fig. 12; Fig. 13 | -   | 40.1  | 49.3 | m $\Omega$    |

| Symbol                                       | Parameter                    | Conditions                                                                                                                                                              |  | Min | Typ  | Max | Unit |
|----------------------------------------------|------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--|-----|------|-----|------|
| <b>Dynamic characteristics FET1 and FET2</b> |                              |                                                                                                                                                                         |  |     |      |     |      |
| $Q_{G(tot)}$                                 | total gate charge            | $I_D = 5\text{ A}$ ; $V_{DS} = 32\text{ V}$ ; $V_{GS} = 10\text{ V}$ ;<br>$T_J = 25\text{ }^\circ\text{C}$ ; Fig. 14; Fig. 15                                           |  | -   | 7.9  | -   | nC   |
| $Q_{GS}$                                     | gate-source charge           |                                                                                                                                                                         |  | -   | 1.5  | -   | nC   |
| $Q_{GD}$                                     | gate-drain charge            | $I_D = 5\text{ A}$ ; $V_{DS} = 32\text{ V}$ ; $V_{GS} = 20\text{ V}$ ;<br>$T_J = 25\text{ }^\circ\text{C}$ ; Fig. 14; Fig. 15                                           |  | -   | 2.6  | -   | nC   |
| $C_{iss}$                                    | input capacitance            | $V_{GS} = 0\text{ V}$ ; $V_{DS} = 25\text{ V}$ ; $f = 1\text{ MHz}$ ;<br>$T_J = 25\text{ }^\circ\text{C}$                                                               |  | -   | 394  | 525 | pF   |
| $C_{oss}$                                    | output capacitance           | $V_{GS} = 0\text{ V}$ ; $V_{DS} = 25\text{ V}$ ; $f = 1\text{ MHz}$ ;<br>$T_J = 25\text{ }^\circ\text{C}$ ; Fig. 16                                                     |  | -   | 107  | 128 | pF   |
| $C_{rss}$                                    | reverse transfer capacitance |                                                                                                                                                                         |  | -   | 76   | 104 | pF   |
| $t_{d(on)}$                                  | turn-on delay time           | $V_{DS} = 32\text{ V}$ ; $R_L = 6.5\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ;<br>$R_{G(ext)} = 5\text{ }\Omega$ ; $T_J = 25\text{ }^\circ\text{C}$ ; $I_D = 5\text{ A}$ |  | -   | 4.4  | -   | ns   |
| $t_r$                                        | rise time                    |                                                                                                                                                                         |  | -   | 4.5  | -   | ns   |
| $t_{d(off)}$                                 | turn-off delay time          |                                                                                                                                                                         |  | -   | 8.3  | -   | ns   |
| $t_f$                                        | fall time                    |                                                                                                                                                                         |  | -   | 5.2  | -   | ns   |
| <b>Source-drain diode FET1 and FET2</b>      |                              |                                                                                                                                                                         |  |     |      |     |      |
| $V_{SD}$                                     | source-drain voltage         | $I_S = 5\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; Fig. 17                                                                                 |  | -   | 0.78 | 1.2 | V    |
| $t_{rr}$                                     | reverse recovery time        | $I_S = 5\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ;<br>$V_{DS} = 20\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$                       |  | -   | 12.4 | -   | ns   |
| $Q_r$                                        | recovered charge             |                                                                                                                                                                         |  | -   | 6.7  | -   | nC   |



**Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values**

$$V_{DS} = 10\text{ V}$$



**Fig. 7. Forward transconductance as a function of drain current; typical values**

$$T_J = 25\text{ }^\circ\text{C}; V_{DS} = 15\text{ V}$$

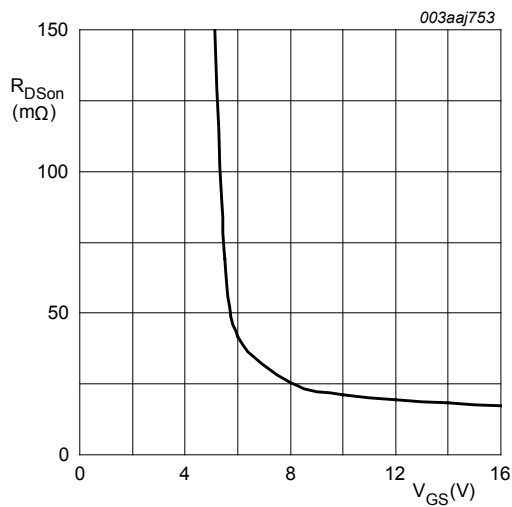


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\text{ °C}; I_D = 5\text{ A}$

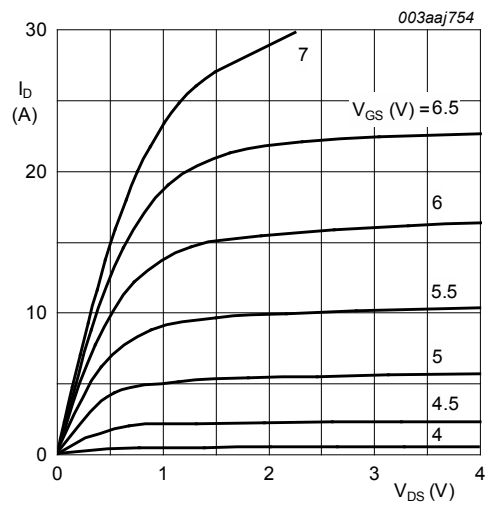


Fig. 9. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25\text{ °C}$

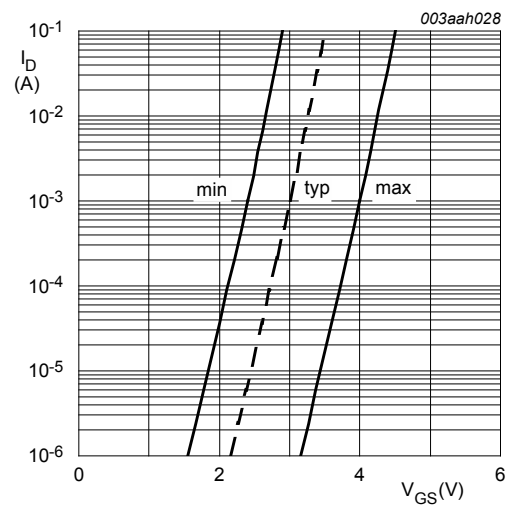


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25\text{ °C}; V_{DS} = 5\text{ V}$

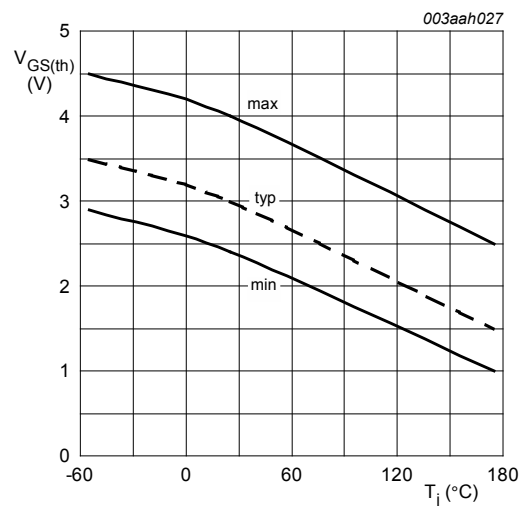


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

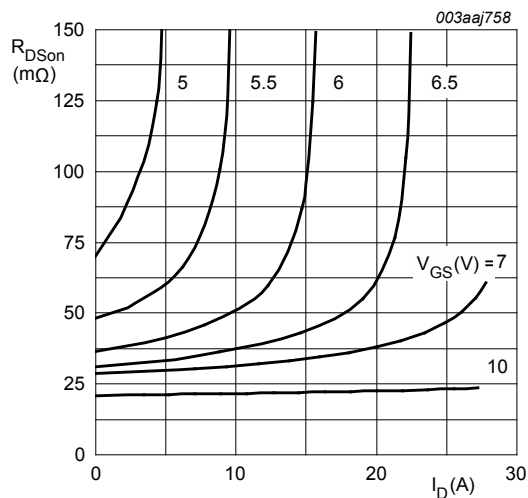


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25\text{ }^{\circ}\text{C}$$

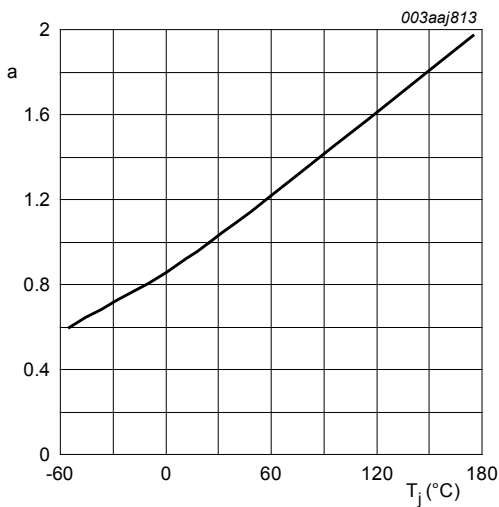


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

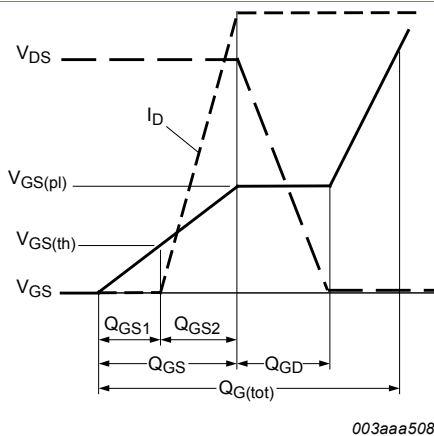


Fig. 14. Gate charge waveform definitions

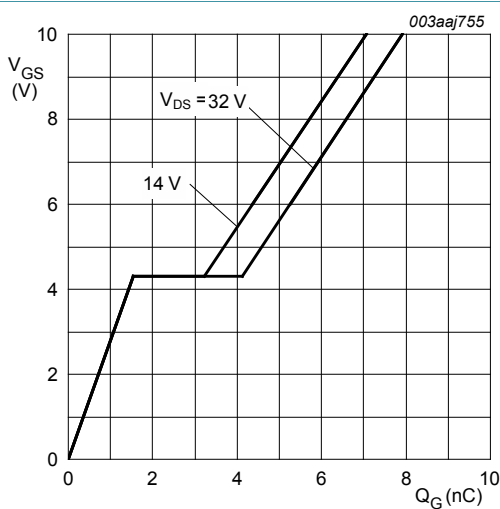


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25\text{ }^{\circ}\text{C}; I_D = 5\text{ A}$$

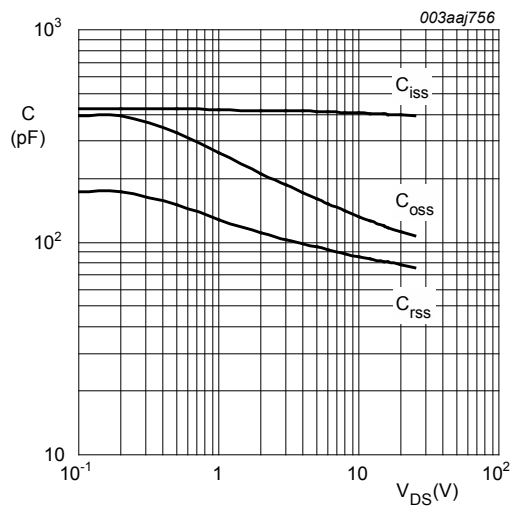


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

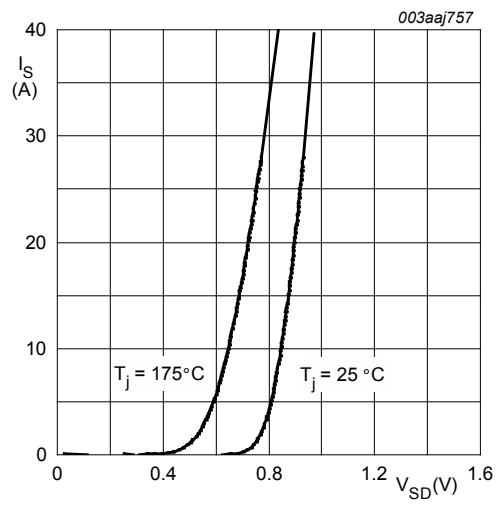


Fig. 17. Source current as a function of source-drain voltage; typical values

$V_{GS} = 0\text{ V}$

11. Package outline

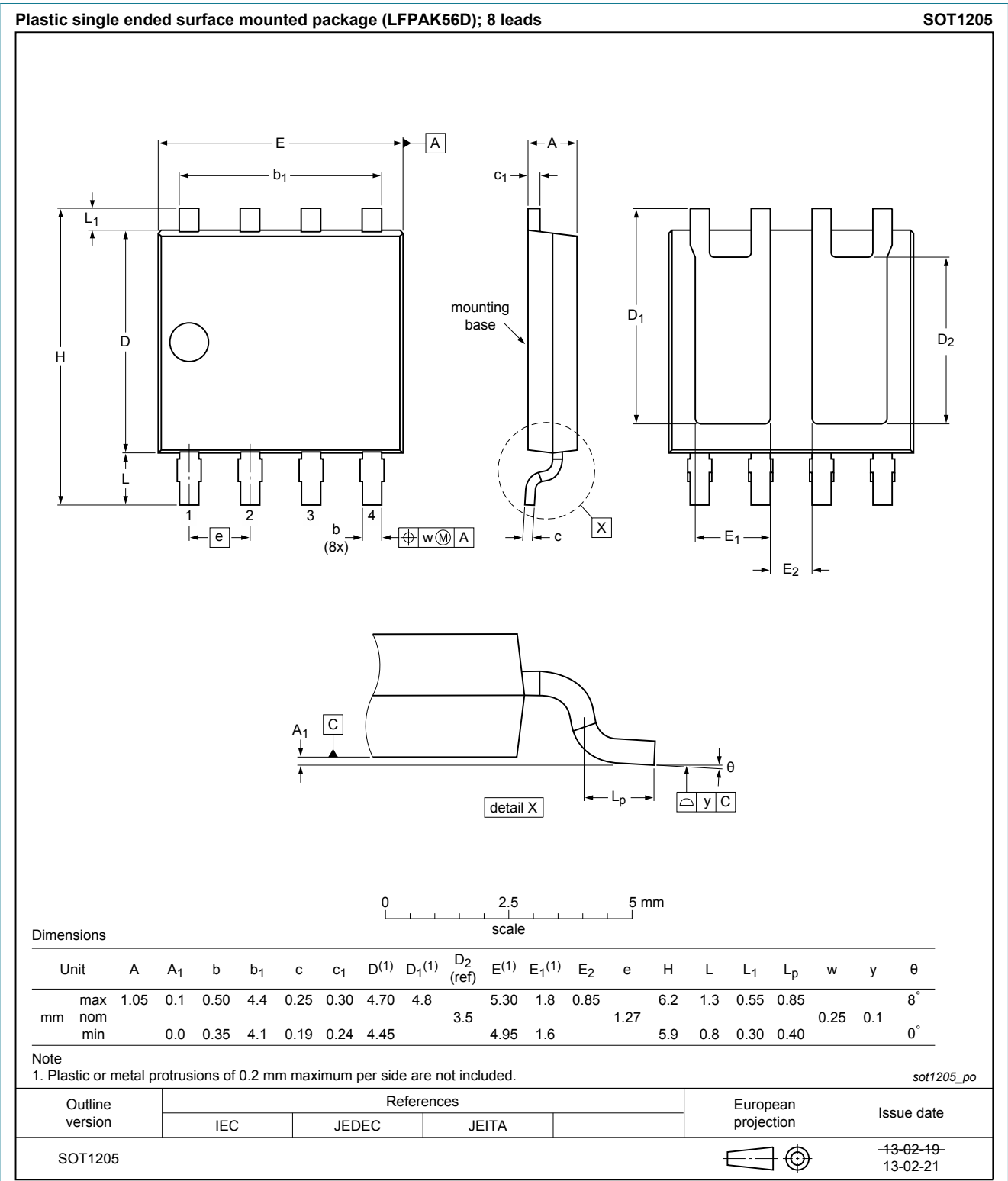


Fig. 18. Package outline LPAK56D (SOT1205)

## 12. Legal information

### 12.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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For more information, please visit: <http://www.nexperia.com>

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